

In re Patent Application of
ZENG
Serial No. Not Yet Assigned
Filed: Herewith

least one device active region for a metal-oxide semiconductor field-effect transistor (MOSFET).

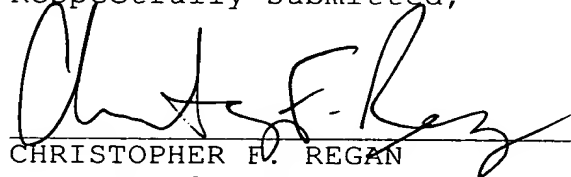
74. A method according to Claim 65 wherein forming the at least one device active region comprises forming at least one device active region for an insulated gate bipolar transistor (IGBT).

75. A method according to Claim 65 wherein forming the at least one device active region comprises forming at least one active region of a microprocessor.

REMARKS

It is believed that all of the claims are patentable over the prior art. Accordingly, after the Examiner completes a thorough examination and finds the claims patentable, a Notice of Allowance is respectfully requested in due course. Should the Examiner determine any minor informalities that need to be addressed, he is encouraged to contact the undersigned attorney at the telephone number below.

Respectfully submitted,



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